

PEMD9

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

29 December 2022

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in an ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PEMH9 PNP/PNP complement: PEMB9

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs

3. Applications

- Low current peripheral driver
- Controlling IC inputs
- · Replacement of general purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor,	Per transistor, for the PNP transistor (TR2) with negative polarity						
V _{CEO}	collector-emitter voltage	open base		-	-	50	V
I _O	output current			-	-	100	mA
R1	bias resistor 1 (input)		[1]	7	10	13	kΩ
R2/R1	bias resistor ratio		[1]	3.7	4.7	5.7	

[1] See section "Test information" for resistor calculation and test conditions.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	6 5 4	
3	O2	output (collector) TR2		R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	0	TR1 R2 R1
6	01	output (collector) TR1	1 2 3	
			SOT666	GND1 I1 O2
				006aaa143

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
PEMD9	SOT666	plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body	<u>SOT666</u>		

7. Marking

Table 4. Marking codes

Type number	Marking code
PEMD9	D9

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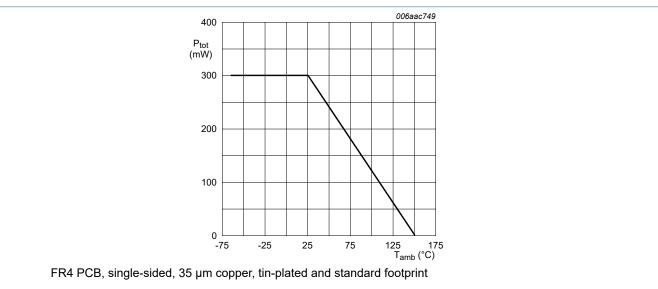
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or, for the PNP transistor (TR	2) with negative polarity			'	
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
VI	input voltage	input voltage TR1		-	40	V
				-	-6	V
		input voltage TR2		-	6	V
				-	-40	V
Io	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] [2]	-	200	mW
Per device	<u> </u>		,	'	'	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] [2]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] [2]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] [2]	-	-	417	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.

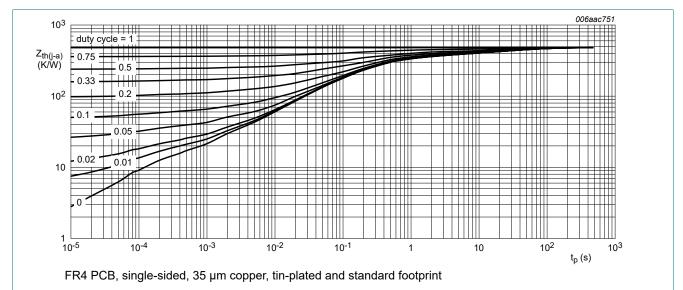


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

10. Characteristics

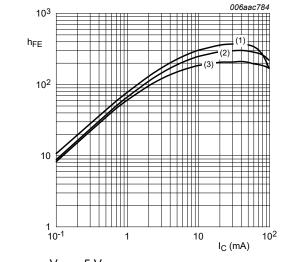
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor (TR2) with negative polarity					
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		50	-	-	V
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
I _{CEO} collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	1	μΑ	
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 mA; T _{amb} = 25 °C		-	-	150	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA; T _{amb} = 25 °C		100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
V _{I(off)}	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	0.7	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 1 mA; T _{amb} = 25 °C		1.4	0.8	-	V
R1	bias resistor 1 (input)		[1]	7	10	13	kΩ
R2/R1	bias resistor ratio		[1]	3.7	4.7	5.7	
TR1 (NPN)							
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	230	-	MHz
TR2 (PNP)				·			
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	180	-	MHz
		'amb 25 0					

^[1] See section "Test information" for resistor calculation and test conditions.

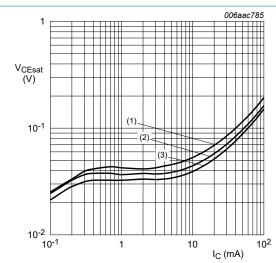
^[2] Characteristics of built-in transistor

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω



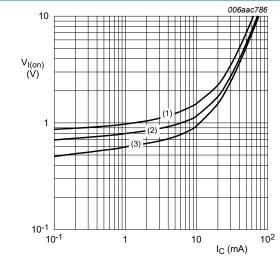
V_{CE} = 5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



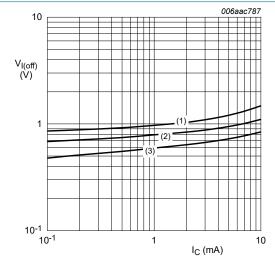
 V_{CE} = 0.3 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 V_{CE} = 5 V

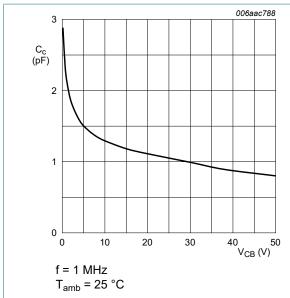
(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

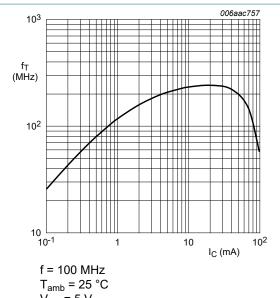
(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

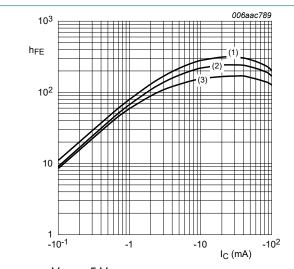


TR1 (NPN): Collector capacitance as a function Fig. 7. of collector-base voltage; typical values



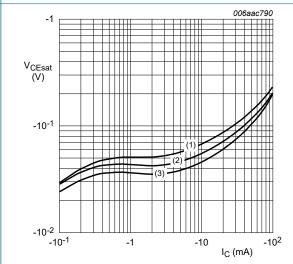
 T_{amb} = 25 °C V_{CE} = 5 V

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



 V_{CE} = -5 V(1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) $T_{amb} = -40 \, ^{\circ}C$

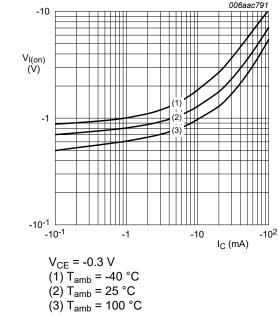
Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values



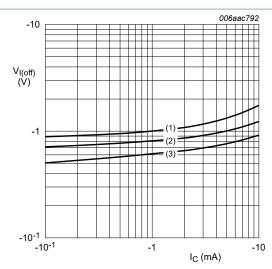
 $I_{\rm C}/I_{\rm B}=20$ (1) T_{amb} = 100 °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω



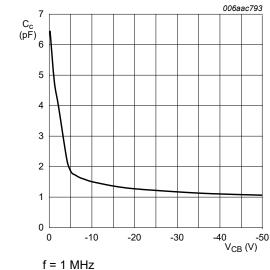
of collector current; typical values



V_{CE} = -5 V (1) T_{amb} = -40 °C (2) T_{amb} = 25 °C

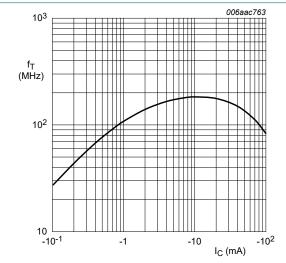
(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 11. TR2 (PNP): On-state input voltage as a function | Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz

 T_{amb} = 25 °C

 $V_{CE} = -5 V$

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

11. Test information

Resistor calculation

• Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I3)}{R1 \cdot I3} - 1$$

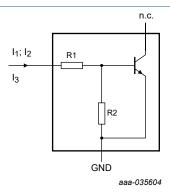


Fig. 15. TR1 (NPN): Resistor test circuit

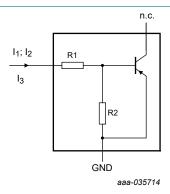


Fig. 16. TR2 (PNP): Resistor test circuit

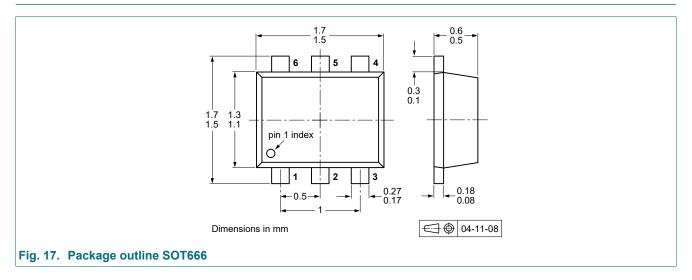
Resistor test conditions

Table 8. Resistor test conditions

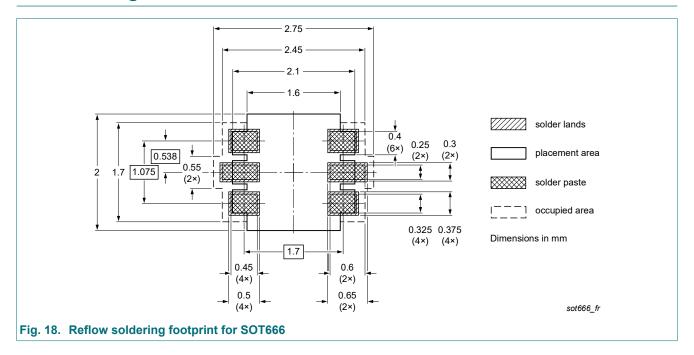
PEMD9	R1 (kΩ)	R2 (kΩ)	Test conditions		
			I ₁	l ₂	l ₃
TR1 (NPN)	10	47	350 μΑ	450 μΑ	-100 μA
TR2 (PNP)	10	47	-350 μΑ	-450 μA	100 μΑ

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

12. Package outline



13. Soldering



10 / 13

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

14. Revision history

Table 9. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PEMD9 v.7	20221229	Product data sheet	-	PEMD9_PUMD9 v.6
Modification:	of Nexperia Legal texts Family data Product(s) of		v company nam data sheet.	mply with the identity guidelines
PEMD9_PUMD9 v.6	20111122	Product data sheet	-	PEMD9_PUMD9 v.5
PEMD9_PUMD9 v.5	20040415	Product data sheet	-	PEMD9_PUMD9 v.4
PEMD9_PUMD9 v.4	20031104	Product specification	-	PEMD9 v.2 PUMD9 v.3
PEMD9 v.2	20020905	Product specification	-	PEMD9 v.1
PEMD9 v.1	20011022	Preliminary specification	-	-
PUMD9 v.3	20010216	Product specification	-	PUMD9 v.2
PUMD9 v.2	19990520	Product specification	-	PUMD9 v.1
PUMD9 v.1	19990107	Product specification	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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